



瑞而美 work steadily

蘇州瑞而美光電科技有限公司

Suzhou Realmay Lightings Tech Co., Ltd

Specification of 2" n-GaN/u-GaN on Sapphire Substrate

Description	Specification
Material	n-GaN / u-GaN on High-Quality and Mono-crystalline Al ₂ O ₃
Wafer Orientation	c-plane off Angle: $0.2^{\circ} \pm 0.1^{\circ}$ to M axis c-plane off Angle: $0^{\circ} \pm 0.1^{\circ}$ to A axis
Pruner Flat Orientation	A-Plane $\pm 0.3^{\circ}$
Primary Flat Length	16 ± 1 mm
Transmissivity	$> 70\%$
Diameter	50.8 ± 0.1 mm
Thickness	430 ± 20 μ m
Front Surface Roughness	Ra ≤ 0.5 nm
Back Surface Roughness	Ra: 0.8~1.2 μ m
Resistivity	< 0.5 ohm.cm
Dislocation density	$< 1 \times 10^9$ cm ⁻²
TTV	≤ 10 μ m
BOW	-10~0 μ m
Warp	≤ 10 μ m
Defective Patterns	Total defective area $\leq 5\%$ of wafer area; Inspection by naked eye added without bright light
Laser Marking	Back surface marked with clear laser number
Packaging	Clean room, vacuum packing

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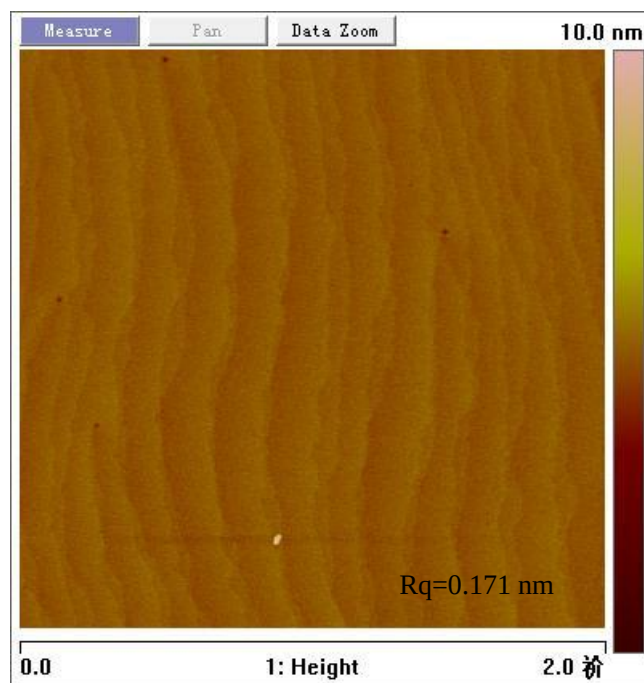
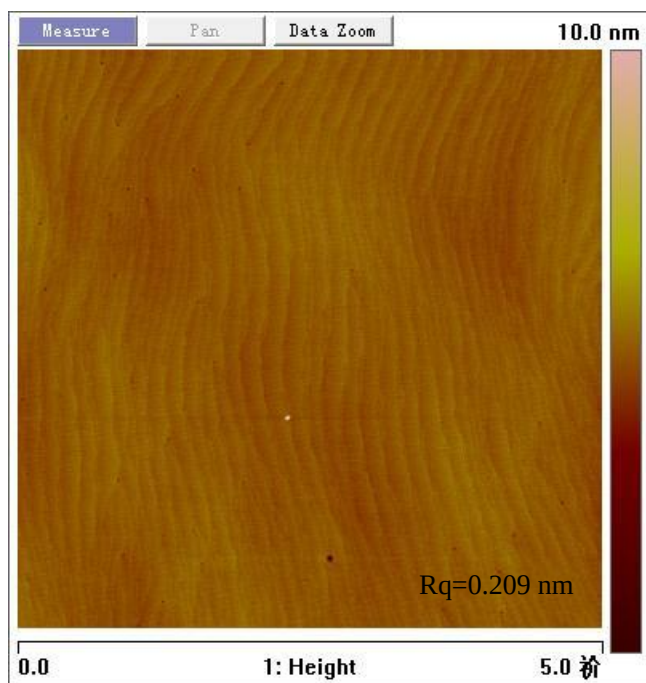
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AFM



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